



#### P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

V <sub>(BR)DSS</sub>	Rds(on)	Ι <sub>D</sub> T <sub>A</sub> = +25°C
-20V	$5\Omega @ V_{GS} = -4.5V$	-200mA
	7Ω @ V <sub>GS</sub> = -2.5V	-170mA
	10Ω @ V <sub>GS</sub> = -1.8V	-140mA
	15Ω @ V <sub>GS</sub> = -1.5V	-50mA

#### Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

#### **Applications**

- DC-DC Converters
- Power Management Functions

#### **Features and Benefits**

- P-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage V<sub>GS(TH)</sub>
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surfaced Mount Package
- Ultra-Low Package Profile, 0.4mm Maximum Package Height
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## Mechanical Data

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @

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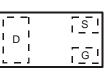
• Weight: 0.001 grams (Approximate)

#### X2-DFN1006-3

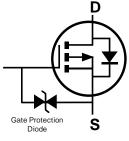




Bottom View



Top View Internal Schematic



Equivalent Circuit

#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP210DUFB4-7	X2-DFN1006-3	3,000/Tape & Reel
DMP210DUFB4-7B	X2-DFN1006-3	10,000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



# Marking Information

DMP210DUFB4-7	From date code 1527 (YYWW), Top View Dot Denotes Drain Side Top View Bar Denotes Gate and Source Side Top View Bar Denotes Gate and Source Side
DMP210DUFB4-7B	For View Bar Denotes Gate and Source Side N1 = Part Marking Code $(+ + + + + + + + + + + + + + + + + + +$



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V <sub>DSS</sub>	-20	V		
Gate-Source Voltage	V <sub>GSS</sub>	±10	V		
Continuous Drain Current (Note 5) $V_{GS}$ = -4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-200 -160	mA
Continuous Drain Current (Note 5) $V_{GS} = -1.8V$	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-140 -110	mA
Pulsed Drain Current	T <sub>P</sub> = 10	μs	I <sub>DM</sub>	-600	mA

## **Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	PD	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	357	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

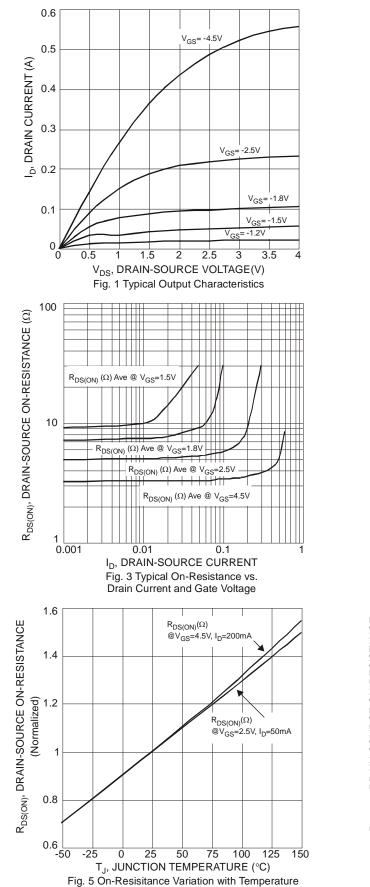
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

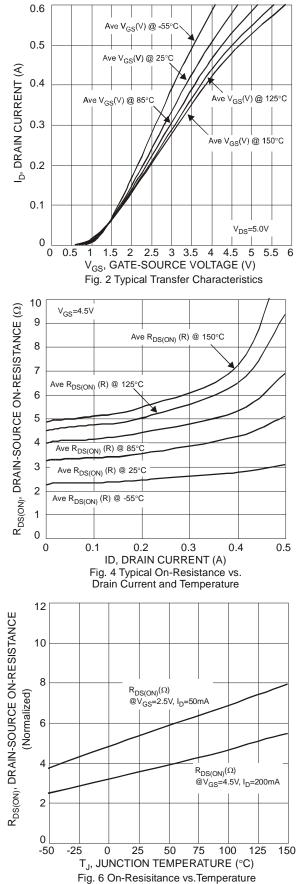
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)		,		71			
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	-20			V	$V_{GS} = 0V, I_D = -250\mu A$
Zara Cata Valtaga Drain Current					-100	nA	$V_{DS} = -16V, V_{GS} = 0V$
Zero Gate Voltage Drain Current		IDSS	_	—	-50	nA	$V_{DS} = -5.0V, V_{GS} = 0V$
					±100	nA	$V_{GS} = \pm 5.0 V, V_{DS} = 0 V$
Gate-Source Leakage		IGSS	—		±1	μΑ μΑ	$V_{GS} = \pm 8.0 V$ , $V_{DS} = 0 V$
					±10		$V_{GS} = \pm 10.0 V$ , $V_{DS} = 0 V$
ON CHARACTERISTICS (Note 6)				-			F
Gate Threshold Voltage	$@T_{J} = +25^{\circ}C$	V <sub>GS(th)</sub>	-0.5		-1.0	V	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$
Gate Threshold Voltage (Note 7)	$@T_J = 0^{\circ}C$		-0.55		-1.05		
	$@T_{J} = +85^{\circ}C$	V <sub>GS(th)</sub>	-0.40	_	-0.90	V	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$
	$@T_J = +100°C$		-0.35		-0.85		
				_	5		$V_{GS} = -4.5V, I_D = -100mA$
		R <sub>DS(ON)</sub>		_	7	Ω	$V_{GS} = -2.5V, I_D = -50mA$
Static Drain-Source On-Resistance			_	_	10		$V_{GS} = -1.8V, I_D = -20mA$
					15		$V_{GS} = -1.5V, I_D = -10mA$
			_	20	_		$V_{GS} = -1.2V, I_{D} = -1mA$
Forward Transfer Admittance		Y <sub>fs</sub>	_	200	—	mS	$V_{DS} = -10V, I_{D} = -200mA$
Diode Forward Voltage (Note 5)		V <sub>SD</sub>	-0.5	_	-1.2	V	$V_{GS} = 0V, I_{S} = -115mA$
DYNAMIC CHARACTERISTICS (N	ote 7)					-	-
Input Capacitance		Ciss		13.72	175	pF	
Output Capacitance		Coss	_	4.01	30	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V - f = 1.0MHz
Reverse Transfer Capacitance		Crss	_	2.34	20	pF	
SWITCHING CHARACTERISTICS	(Note 7)					-	
Turn-On Delay Time		t <sub>d(on)</sub>	—	7.7			
Rise Time		tr	_	19.3	_	nS	$V_{GS} = -4.5V, V_{DD} = -15V$ $I_D = -180mA, R_G = 2.0\Omega$
Turn-Off Delay Time		t <sub>d(off)</sub>		25.9	_	113	
Fall Time		t <sub>f</sub>	_	31.5	_		

 Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing. Notes:

## DMP210DUFB4

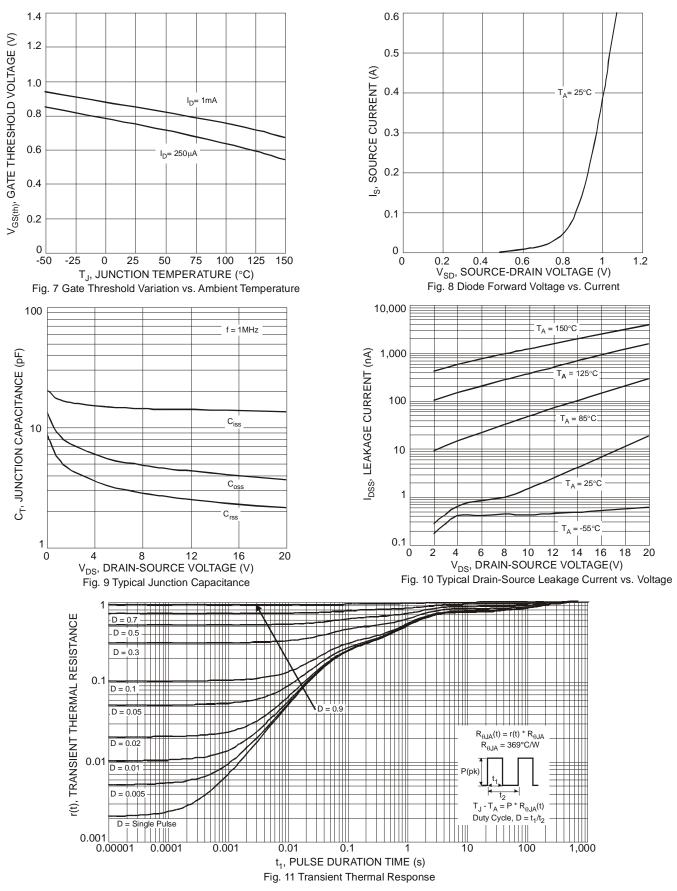






#### DMP210DUFB4

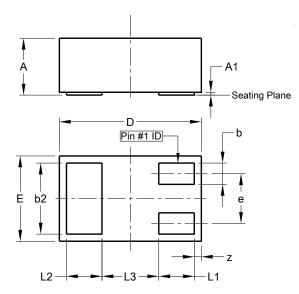






## **Package Outline Dimensions**

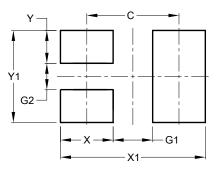
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN1006-3						
Dim	Min	Max	Тур			
Α		0.40				
A1	0.00	0.05	0.03			
b	0.10	0.20	0.15			
b2	0.45	0.55	0.50			
D	0.95	1.05	1.00			
Е	0.55	0.65	0.60			
е	1	-   -				
L1	0.20	0.30	0.25			
L2	0.20	0.30	0.25			
L3	-	-	0.40			
z	0.02	0.08	0.05			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



#### X2-DFN1006-3

X2-DFN1006-3

Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



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